

TO-92 Plastic-Encapsulate Transistors

FEATURES

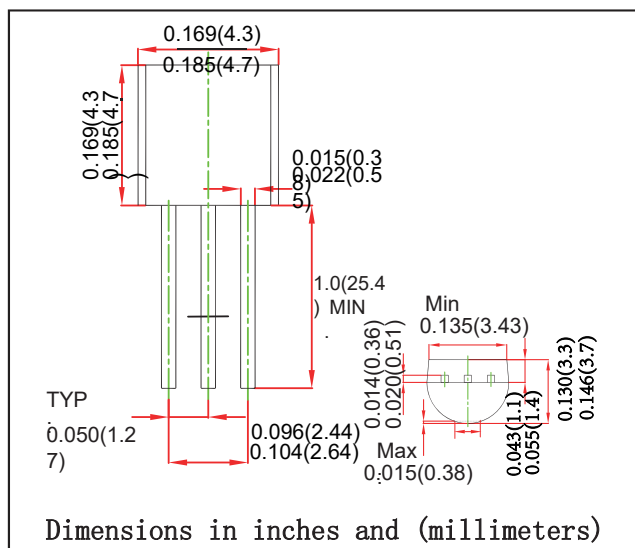
- High Forward Current Transfer Ratio h_{FE}
- Low Collector to Emitter Saturation Voltage $V_{CE(sat)}$
- Allowing Supply with the Radial Taping
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

MAXIMUM RATINGS AND CHARACTERISTICS

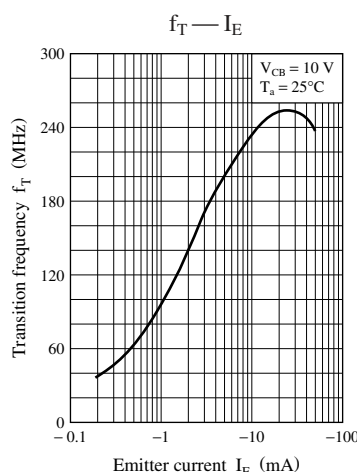
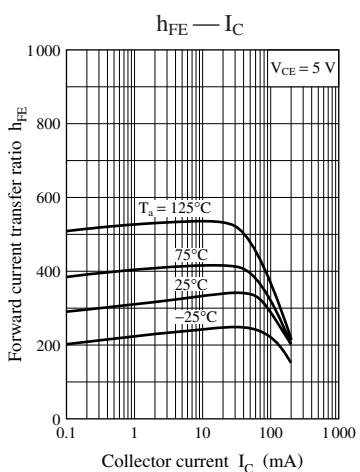
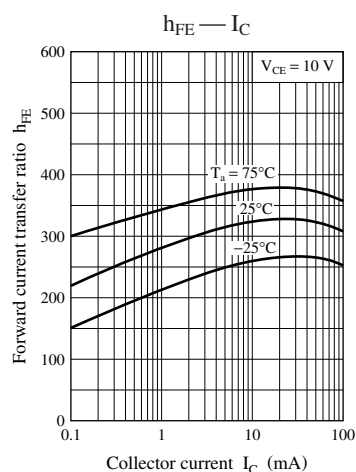
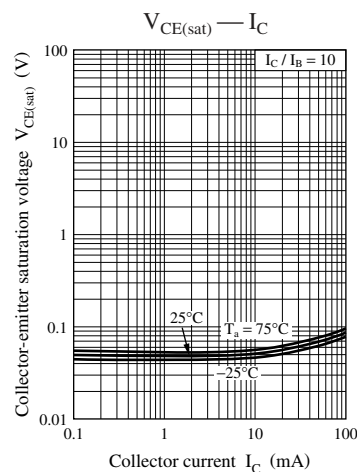
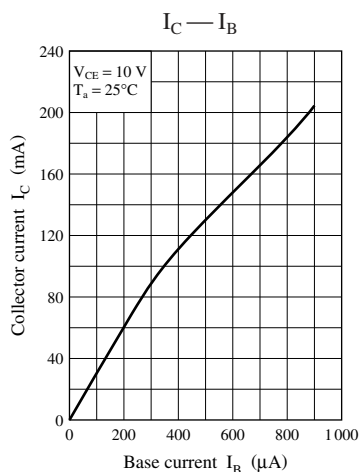
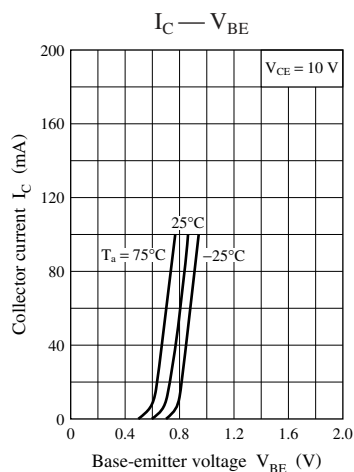
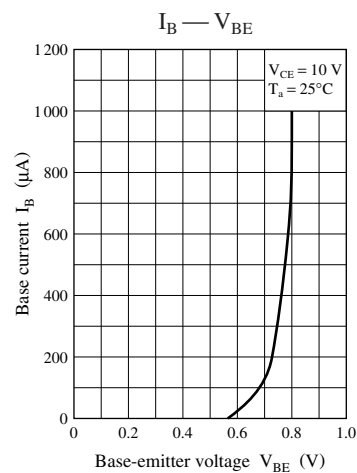
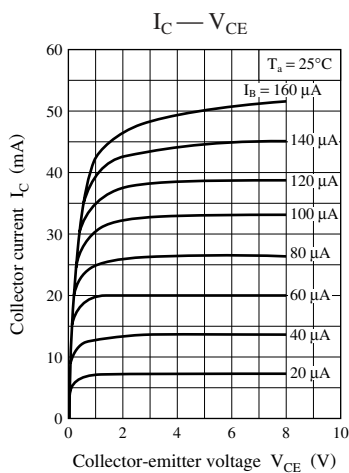
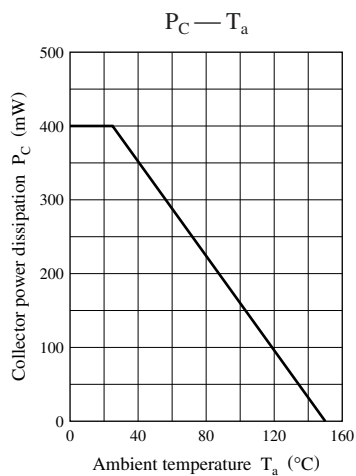
@ 25°C Ambient Temperature (unless otherwise noted)



Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current -Continuous	I_C	100	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=2mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=2mA$	160		460	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=100mA$	90			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.3	V
Transition frequency	f_T	$V_{CE}=10V, I_C=2mA, f=200MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	3.5			pF

RATINGS AND CHARACTERISTIC CURVES



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